

## N-Channel 900V (D-S) Super Junction Power MOSFET

### PRODUCT SUMMARY

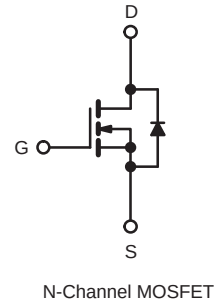
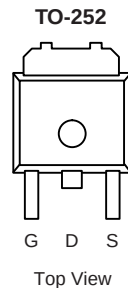
|                           |                        |     |
|---------------------------|------------------------|-----|
| $V_{DS}$ (V)              | 900                    |     |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10\text{ V}$ | 2.7 |
| $Q_g$ (Max.) (nC)         | 200                    |     |
| $Q_{gs}$ (nC)             | 24                     |     |
| $Q_{gd}$ (nC)             | 110                    |     |
| Configuration             | Single                 |     |

### FEATURES

- Dynamic  $dV/dt$  Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



Available  
**RoHS\***  
 COMPLIANT



### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

| PARAMETER                                        |                         |                         | SYMBOL                            | LIMIT            | UNIT     |
|--------------------------------------------------|-------------------------|-------------------------|-----------------------------------|------------------|----------|
| Drain-Source Voltage                             |                         |                         | V <sub>DS</sub>                   | 900              | V        |
| Gate-Source Voltage                              |                         |                         | V <sub>GS</sub>                   | ± 20             |          |
| Continuous Drain Current                         | V <sub>GS</sub> at 10 V | T <sub>C</sub> = 25 °C  | I <sub>D</sub>                    | 2.0              | A        |
|                                                  |                         | T <sub>C</sub> = 100 °C |                                   | 1.5              |          |
| Pulsed Drain Current <sup>a</sup>                |                         |                         | I <sub>DM</sub>                   | 8.0              |          |
| Linear Derating Factor                           |                         |                         |                                   | 1.5              | W/°C     |
| Single Pulse Avalanche Energy <sup>b</sup>       |                         |                         | E <sub>AS</sub>                   | 470              | mJ       |
| Repetitive Avalanche Current <sup>a</sup>        |                         |                         | I <sub>AR</sub>                   | 4.8              | A        |
| Repetitive Avalanche Energy <sup>a</sup>         |                         |                         | E <sub>AR</sub>                   | 19               | mJ       |
| Maximum Power Dissipation                        | T <sub>C</sub> = 25 °C  |                         | P <sub>D</sub>                    | 120              | W        |
| Peak Diode Recovery dV/dt <sup>c</sup>           |                         |                         | dV/dt                             | 2.0              | V/ns     |
| Operating Junction and Storage Temperature Range |                         |                         | T <sub>J</sub> , T <sub>stg</sub> | - 55 to + 150    | °C       |
| Soldering Recommendations (Peak Temperature)     |                         | for 10 s                |                                   | 300 <sup>d</sup> |          |
| Mounting Torque                                  | 6-32 or M3 screw        |                         |                                   | 10               | lbf · in |
|                                                  |                         |                         |                                   | 1.1              | N · m    |

### Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
 b.  $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 23\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 7.8\text{ A}$  (see fig. 12).  
 c.  $I_{SD} \leq 7.8\text{ A}$ ,  $dI/dt \leq 140\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq 600\text{ V}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .  
 d. 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

**THERMAL RESISTANCE RATINGS**

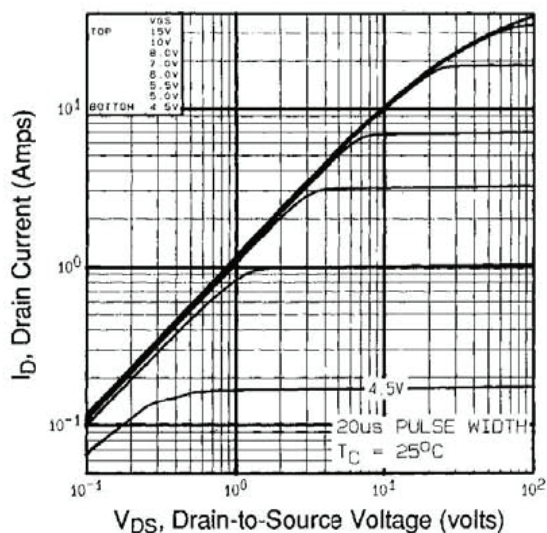
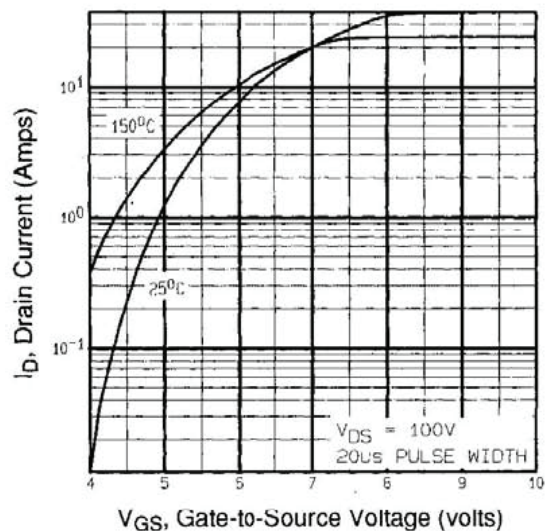
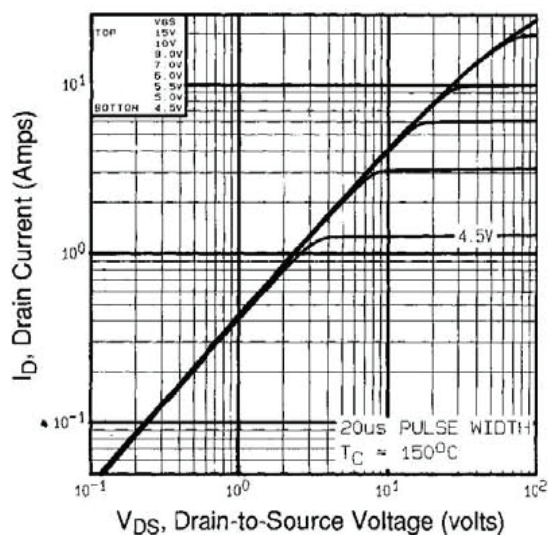
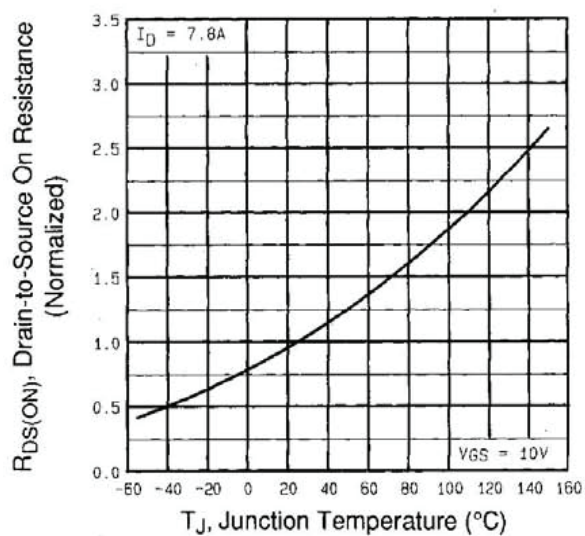
| PARAMETER                           | SYMBOL     | TYP. | MAX. | UNIT |
|-------------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient         | $R_{thJA}$ | -    | 40   | °C/W |
| Case-to-Sink, Flat, Greased Surface | $R_{thCS}$ | 0.24 | -    |      |
| Maximum Junction-to-Case (Drain)    | $R_{thJC}$ | -    | 0.65 |      |

**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

| PARAMETER                                 | SYMBOL              | TEST CONDITIONS                                                                                                                                                     |                                                                                    | MIN. | TYP. | MAX.      | UNIT                |
|-------------------------------------------|---------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------|------|------|-----------|---------------------|
| Static                                    |                     |                                                                                                                                                                     |                                                                                    |      |      |           |                     |
| Drain-Source Breakdown Voltage            | $V_{DS}$            | $V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                              |                                                                                    | 900  | -    | -         | V                   |
| $V_{DS}$ Temperature Coefficient          | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$                                                                                                       |                                                                                    | -    | 0.98 | -         | V/ $^\circ\text{C}$ |
| Gate-Source Threshold Voltage             | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                                  |                                                                                    | 2.0  | -    | 4.0       | V                   |
| Gate-Source Leakage                       | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$                                                                                                                                          |                                                                                    | -    | -    | $\pm 100$ | nA                  |
| Zero Gate Voltage Drain Current           | $I_{DSS}$           | $V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                                                     |                                                                                    | -    | -    | 100       | $\mu\text{A}$       |
|                                           |                     | $V_{DS} = 640\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$                                                                                 |                                                                                    | -    | -    | 500       |                     |
| Drain-Source On-State Resistance          | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$                                                                                                                                              | $I_D = 1.7\text{ A}^b$                                                             | -    | 2.7  | -         | $\Omega$            |
| Forward Transconductance                  | $g_{fs}$            | $V_{DS} = 100\text{ V}$ , $I_D = 1.7\text{ A}^b$                                                                                                                    |                                                                                    | 5.6  | -    | -         | S                   |
| Dynamic                                   |                     |                                                                                                                                                                     |                                                                                    |      |      |           |                     |
| Input Capacitance                         | $C_{iss}$           | $V_{GS} = 0\text{ V}$ ,<br>$V_{DS} = 25\text{ V}$ ,<br>$f = 1.0\text{ MHz}$ , see fig. 5                                                                            |                                                                                    | -    | 1800 | -         | pF                  |
| Output Capacitance                        | $C_{oss}$           |                                                                                                                                                                     |                                                                                    | -    | 500  | -         |                     |
| Reverse Transfer Capacitance              | $C_{rss}$           |                                                                                                                                                                     |                                                                                    | -    | 290  | -         |                     |
| Total Gate Charge                         | $Q_g$               | $V_{GS} = 10\text{ V}$                                                                                                                                              | $I_D = 1.8\text{ A}$ , $V_{DS} = 400\text{ V}$ ,<br>see fig. 6 and 13 <sup>b</sup> | -    | -    | 200       | nC                  |
| Gate-Source Charge                        | $Q_{gs}$            |                                                                                                                                                                     |                                                                                    | -    | -    | 24        |                     |
| Gate-Drain Charge                         | $Q_{gd}$            |                                                                                                                                                                     |                                                                                    | -    | -    | 110       |                     |
| Turn-On Delay Time                        | $t_{d(on)}$         | $V_{DD} = 400\text{ V}$ , $I_D = 1.8\text{ A}$ ,<br>$R_g = 6.2\text{ }\Omega$ , $R_D = 52\text{ }\Omega$<br>see fig. 10 <sup>b</sup>                                |                                                                                    | -    | 19   | -         | ns                  |
| Rise Time                                 | $t_r$               |                                                                                                                                                                     |                                                                                    | -    | 38   | -         |                     |
| Turn-Off Delay Time                       | $t_{d(off)}$        |                                                                                                                                                                     |                                                                                    | -    | 120  | -         |                     |
| Fall Time                                 | $t_f$               |                                                                                                                                                                     |                                                                                    | -    | 39   | -         |                     |
| Internal Drain Inductance                 | $L_D$               | Between lead,<br>6 mm (0.25") from<br>package and center of<br>die contact<br> |                                                                                    | -    | 5.0  | -         | nH                  |
| Internal Source Inductance                | $L_S$               |                                                                                                                                                                     |                                                                                    | -    | 13   | -         |                     |
| Drain-Source Body Diode Characteristics   |                     |                                                                                                                                                                     |                                                                                    |      |      |           |                     |
| Continuous Source-Drain Diode Current     | $I_S$               | MOSFET symbol<br>showing the<br>integral reverse<br>p - n junction diode<br>   |                                                                                    | -    | -    | 5.0       | A                   |
| Pulsed Diode Forward Current <sup>a</sup> | $I_{SM}$            |                                                                                                                                                                     |                                                                                    | -    | -    | 21        |                     |
| Body Diode Voltage                        | $V_{SD}$            | $T_J = 25\text{ }^\circ\text{C}$ , $I_S = 1.8\text{ A}$ , $V_{GS} = 0\text{ V}^b$                                                                                   |                                                                                    | -    | -    | 1.8       | V                   |
| Body Diode Reverse Recovery Time          | $t_{rr}$            | $T_J = 25\text{ }^\circ\text{C}$ , $I_F = 1.8\text{ A}$ ,<br>$di/dt = 100\text{ A}/\mu\text{s}^b$                                                                   |                                                                                    | -    | 650  | 980       | ns                  |
| Body Diode Reverse Recovery Charge        | $Q_{rr}$            |                                                                                                                                                                     |                                                                                    | -    | 3.8  | 5.7       | $\mu\text{C}$       |
| Forward Turn-On Time                      | $t_{on}$            | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )                                                                                     |                                                                                    |      |      |           |                     |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
 b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^{\circ}\text{C}$** 

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^{\circ}\text{C}$** 

**Fig. 4 - Normalized On-Resistance vs. Temperature**

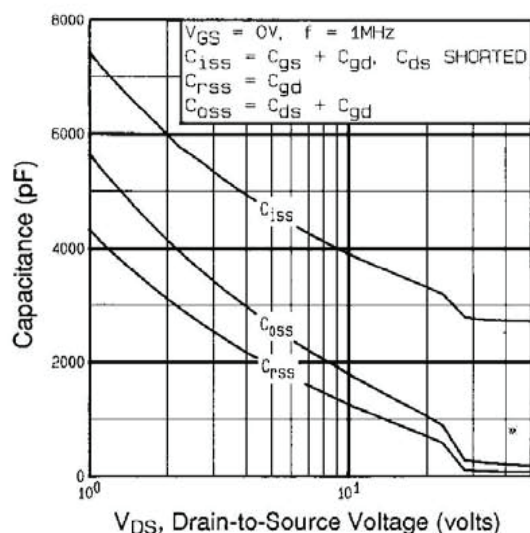


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

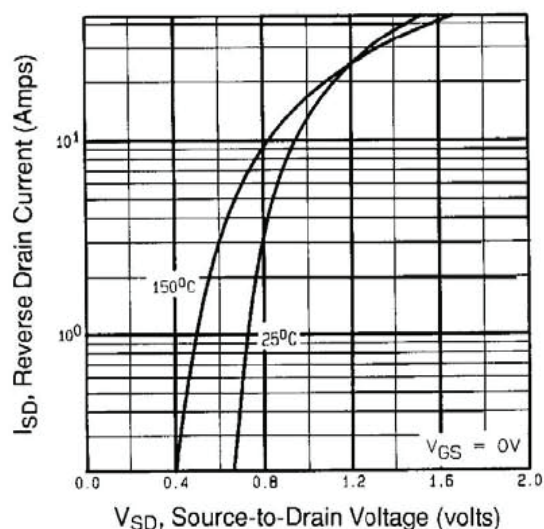


Fig. 7 - Typical Source-Drain Diode Forward Voltage

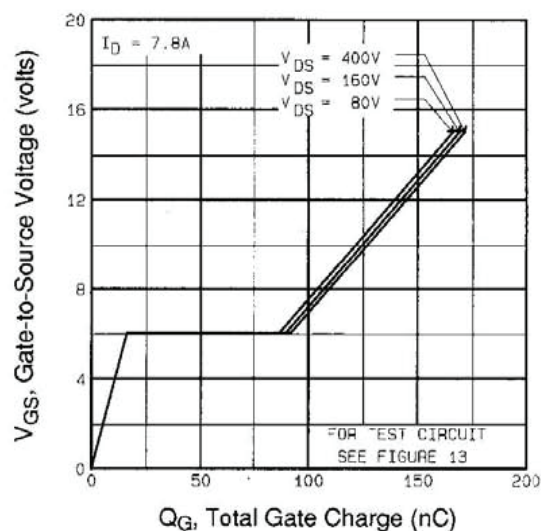


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

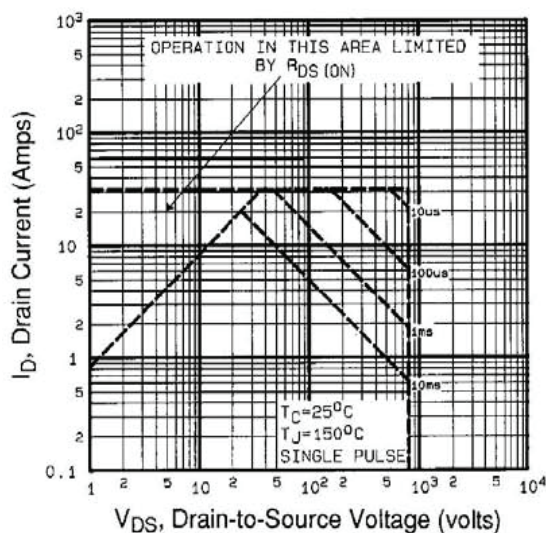


Fig. 8 - Maximum Safe Operating Area

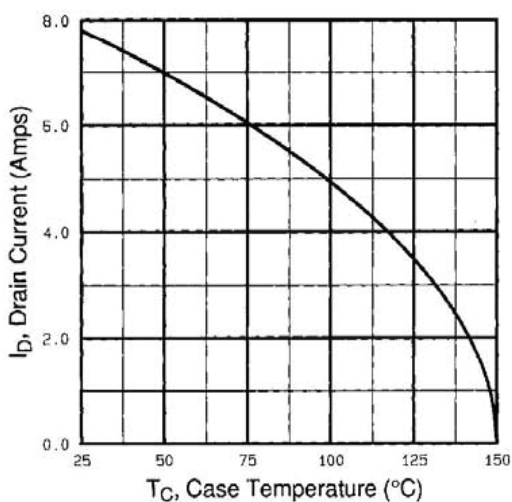


Fig. 9 - Maximum Drain Current vs. Case Temperature

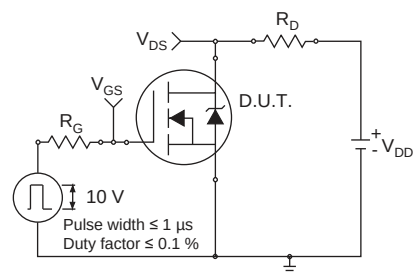


Fig. 10a - Switching Time Test Circuit

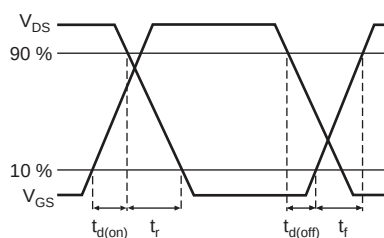


Fig. 10b - Switching Time Waveforms

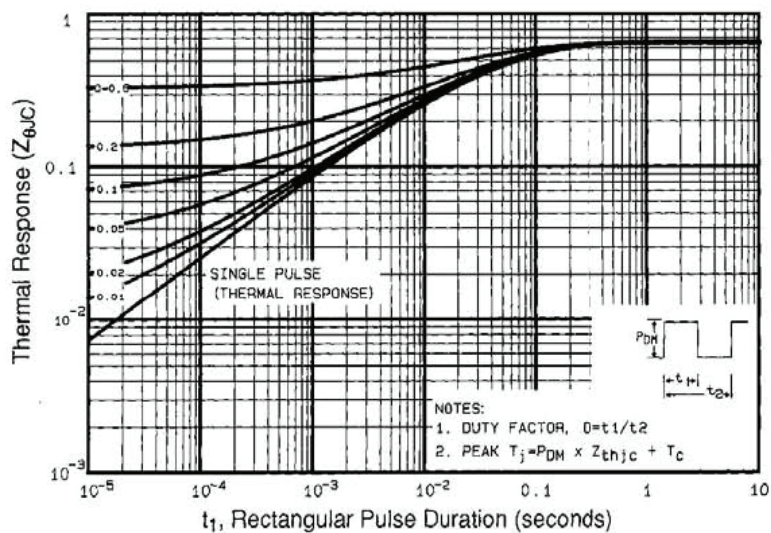


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



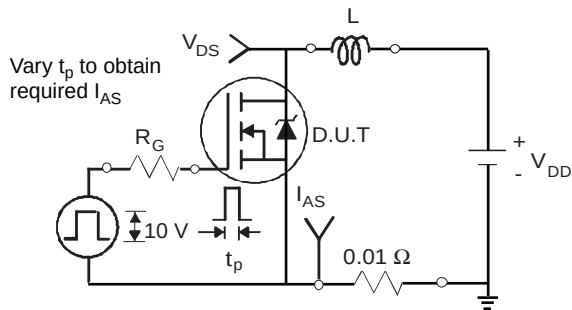


Fig. 12a - Unclamped Inductive Test Circuit

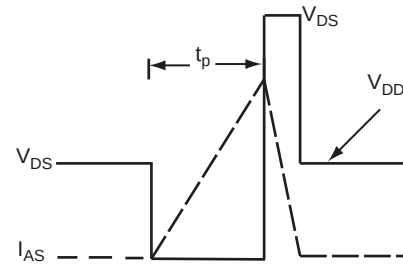


Fig. 12b - Unclamped Inductive Waveforms

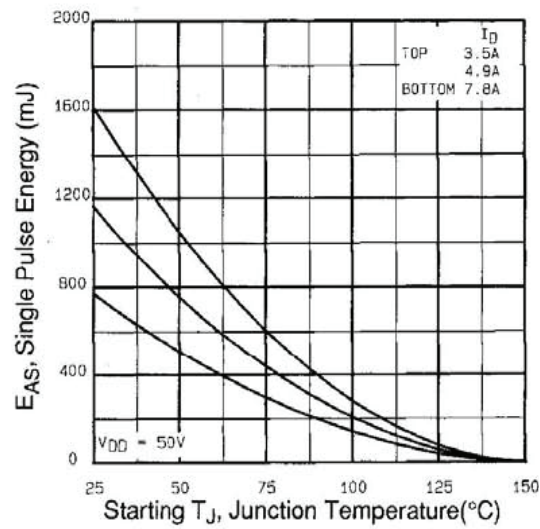


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

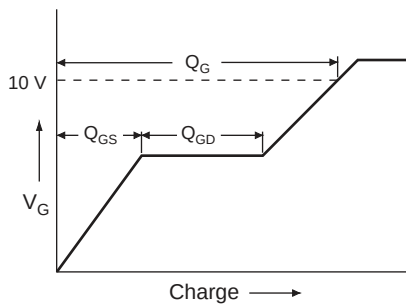


Fig. 13a - Basic Gate Charge Waveform

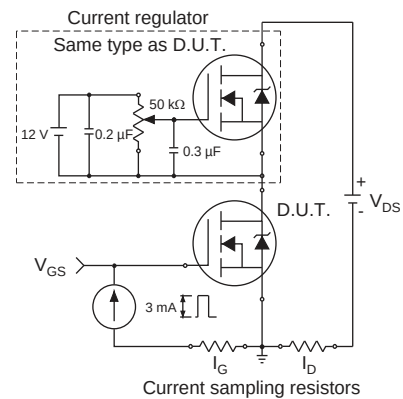
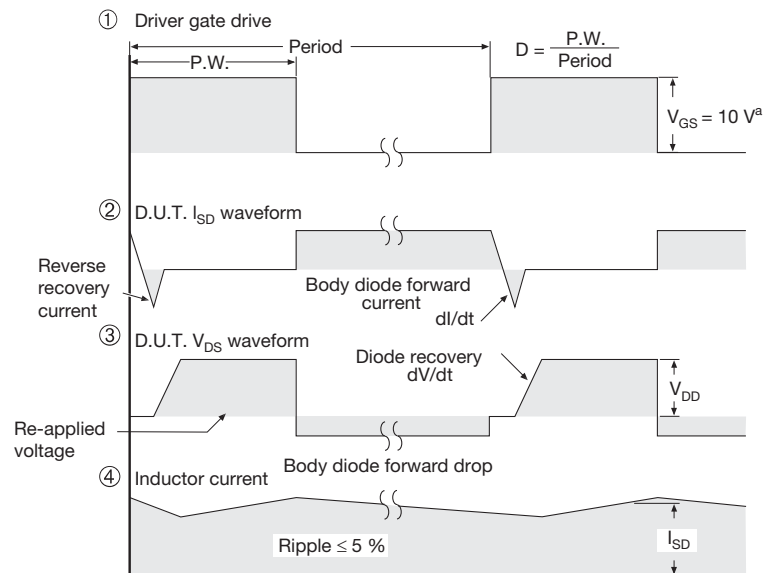
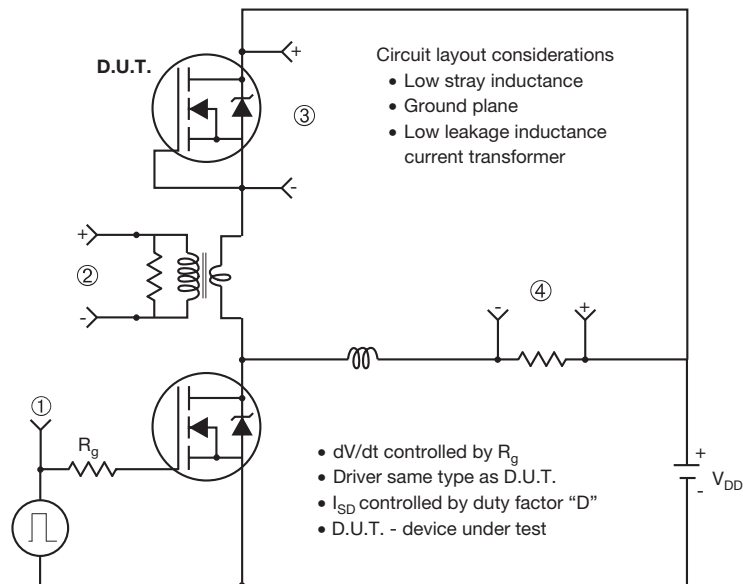


Fig. 13b - Gate Charge Test Circuit

### Peak Diode Recovery $dV/dt$ Test Circuit

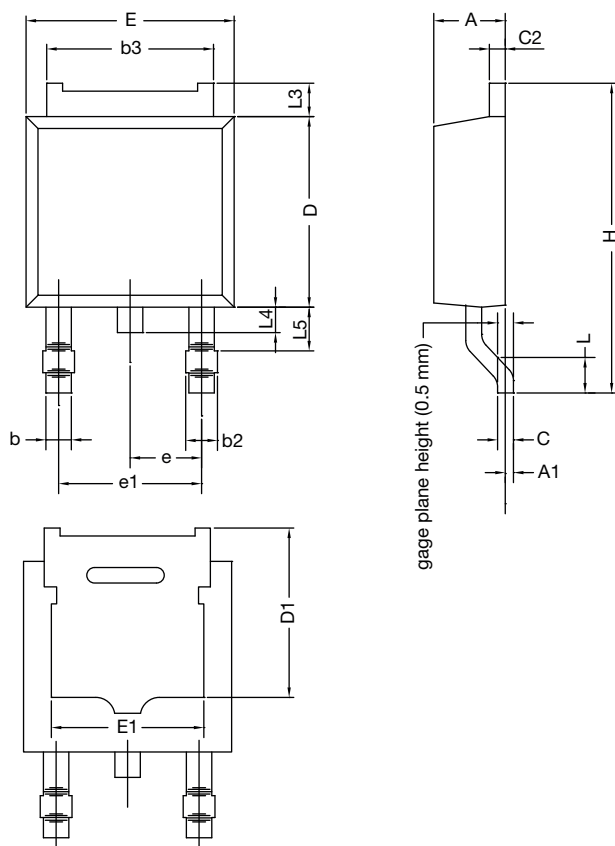


#### Note

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

## TO-252AA CASE OUTLINE



| DIM.                                         | MILLIMETERS |       | INCHES    |       |
|----------------------------------------------|-------------|-------|-----------|-------|
|                                              | MIN.        | MAX.  | MIN.      | MAX.  |
| A                                            | 2.18        | 2.38  | 0.086     | 0.094 |
| A1                                           | -           | 0.127 | -         | 0.005 |
| b                                            | 0.64        | 0.88  | 0.025     | 0.035 |
| b2                                           | 0.76        | 1.14  | 0.030     | 0.045 |
| b3                                           | 4.95        | 5.46  | 0.195     | 0.215 |
| C                                            | 0.46        | 0.61  | 0.018     | 0.024 |
| C2                                           | 0.46        | 0.89  | 0.018     | 0.035 |
| D                                            | 5.97        | 6.22  | 0.235     | 0.245 |
| D1                                           | 5.21        | -     | 0.205     | -     |
| E                                            | 6.35        | 6.73  | 0.250     | 0.265 |
| E1                                           | 4.32        | -     | 0.170     | -     |
| H                                            | 9.40        | 10.41 | 0.370     | 0.410 |
| e                                            | 2.28 BSC    |       | 0.090 BSC |       |
| e1                                           | 4.56 BSC    |       | 0.180 BSC |       |
| L                                            | 1.40        | 1.78  | 0.055     | 0.070 |
| L3                                           | 0.89        | 1.27  | 0.035     | 0.050 |
| L4                                           | -           | 1.02  | -         | 0.040 |
| L5                                           | 1.14        | 1.52  | 0.045     | 0.060 |
| ECN: X12-0247-Rev. M, 24-Dec-12<br>DWG: 5347 |             |       |           |       |

### Note

- Dimension L3 is for reference only.



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